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## **CLAIMS**

1. A method for detecting an endpoint during a chemical mechanical polishing (CMP) process, comprising the operations of:

receiving a current reflected spectrum data sample corresponding to a plurality of spectrums of light reflected from an illuminated portion of a surface of a wafer;

normalizing the current reflected spectrum data sample using a normalization reference comprising a first reflected spectrum data sample obtained earlier during the CMP process; and

updating the normalization reference using a second reflected spectrum data sample obtained earlier during the CMP process, wherein the second reflected spectrum data sample is obtained after the first reflected spectrum data sample.

- 2. A method as recited in claim 1, further comprising the operation of determining an endpoint based on optical interference occurring in the reflected spectrum data.
- 3. A method as recited in claim 1, wherein the first reflected spectrum data sample trails the current reflected spectrum data sample by a predetermined trailing reference delay.

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- 4. A method as recited in claim 3, wherein the trailing reference delay is a number representing an amount of reflectance data samples between the current reflected spectrum data sample and the first reflected spectrum data sample.
- 5. A method as recited in claim 3, further comprising the operation of receiving a new current reflected spectrum data sample corresponding to a plurality of spectrums of light reflected from the illuminated portion of the surface of the wafer at a later time.
- 6. A method as recited in claim 5, wherein the second reflected spectrum data sample trails the new current reflected spectrum data sample by the trailing reference delay.
- 7. A method as recited in claim 2, wherein the optical interference is a result of phase differences in light reflected from different layers of the wafer.
  - 8. A method as recited in claim 7, wherein the optical interference occurs when a top metal layer is reduced to a thin metal zone.

- 9. A method as recited in claim 8, further comprising the operation of determining when oscillations occur in a plot of wave-numbers based on the reflected spectrum data.
- 5 10. A method as recited in claim 9, wherein the endpoint occurs when the oscillations in the plot of wave-numbers occurs.
  - 11. A method for detecting an endpoint during a chemical mechanical polishing (CMP) process, comprising the operations of:
  - receiving a current reflected spectrum data sample corresponding to a plurality of spectrums of light reflected from an illuminated portion of a surface of a wafer;

selecting a first median reflected spectrum data sample from a first plurality of reflected spectrum data samples obtained earlier during the CMP process;

normalizing the current reflected spectrum data sample using a normalization reference comprising the median reflected spectrum data sample; and

updating the normalization reference using a second median reflected spectrum data sample selected from a second plurality of reflected spectrum data samples obtained earlier during the CMP process.

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- 12. A method as recited in claim 11, further comprising the operation of determining an endpoint based on optical interference occurring in the reflected spectrum data.
- 5 13. A method as recited in claim 11, wherein the first plurality of reflected spectrum data samples comprise three consecutive reflected spectrum data samples obtained earlier during the CMP process.
  - 14. A method as recited in claim 13, wherein one of the first plurality of reflected spectrum data samples trails the current reflected spectrum data sample by a predetermined trailing reference delay.
  - 15. A method as recited in claim 14, wherein the trailing reference delay is a number representing an amount of reflectance data samples between the current reflected spectrum data sample and one of the first plurality of reflected spectrum data samples.
  - 16. A method for detecting an endpoint during a chemical mechanical polishing process, comprising the operations of:

illuminating a portion of a surface of a wafer with broad band light;

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receiving a current reflected spectrum data sample corresponding to a plurality of spectrums of light reflected from the illuminated portion of the surface of the wafer;

normalizing the current reflected spectrum data sample using a normalization reference comprising a first reflected spectrum data sample obtained earlier during the CMP process;

determining an endpoint based on optical interference occurring in the reflected spectrum data; and

updating the normalization reference using a second reflected spectrum data sample obtained earlier during the CMP process, wherein the second reflected spectrum data sample is obtained after the first reflected spectrum data sample.

- 17. A method as recited in claim 16, wherein the first reflected spectrum data sample trails the current reflected spectrum data sample by a predetermined trailing reference delay.
- 18. A method as recited in claim 17, wherein the trailing reference delay is a number representing an amount of reflectance data samples between the current reflected spectrum data sample and the first reflected spectrum data sample.

19. A method as recited in claim 18, further comprising the operation of receiving a new current reflected spectrum data sample corresponding to a plurality of spectrums of light reflected from the illuminated portion of the surface of the wafer at a later time.

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20. A method as recited in claim 19, wherein the second reflected spectrum data sample trails the new current reflected spectrum data sample by the trailing reference delay.